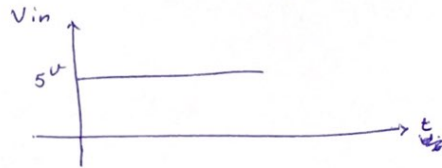
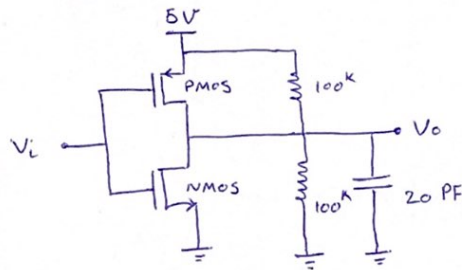


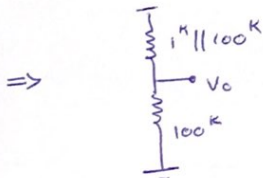
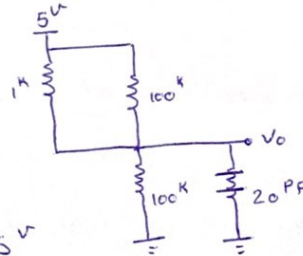
4-35

$$\begin{cases} R_{n-mos} = 200 \Omega \\ R_{p-mos} = 1 K \\ k = 0.2 \frac{mA}{V^2} \\ |V_{th}| = 1 V \end{cases}$$



for ~~xxx~~ $t < 0 \rightarrow \begin{cases} PMOS : ON \\ NMOS : off \end{cases}$

\Rightarrow



$$V_o(t < 0) = \frac{100k \times 5}{100k + (1k \parallel 100k)} = 4.95 V$$

$$\Rightarrow V_{OS, PMOS} = 4.95 - 5 = -0.05 V > \underbrace{V_{GS} - V_{th}}_{-5 - 1 = -6 V}$$

فرض نموده PMOS در حالت ترانزیست درستی باشد.

for $t = 0 : \begin{cases} PMOS : off \\ NMOS : ON \end{cases}$

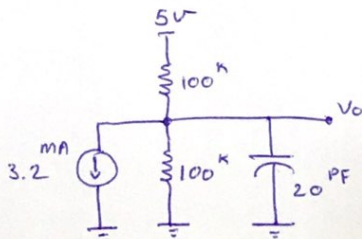
$$\Rightarrow V_{OS, NMOS} = V_{O, PMOS} = 4.95 V$$

$$V_{GS, NMOS} = 5 V \Rightarrow V_{OS} \geq V_{GS} - V_{th}$$

نمونه اشباع می شود

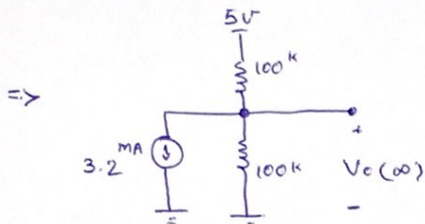
$$I_D = k(V_{GS} - V_{th})^2 = 0.2(5 - 1)^2 = 3.2 mA$$

\Rightarrow



$$V_o(t^-) = V_o(t^+) = 4.95 V$$

$$V_o(\infty) \rightarrow C : open$$

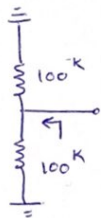


$$KCL: \frac{V_O(\infty) - 0}{100^k} + \frac{V_O(\infty) - 5}{100^k} + 3.2^{mA} = 0$$

$$\Rightarrow V_O(\infty) \cdot \left(\frac{1}{100^k} + \frac{1}{100^k} \right) = \frac{5}{100^k} - 3.2^{mA}$$

$$\Rightarrow V_O(\infty) = \frac{0.05 - 3.2^m}{0.02^k} = -157.5^V$$

$$\tau_1 = R_{TH} \cdot C_{TH}$$



$$R_{TH} = 100^k \parallel 100^k = 50^k$$

$$C_{TH} = 20^{pF} \Rightarrow \tau = 50^k \times 20^p = 100^{nS} = 1^{uS}$$

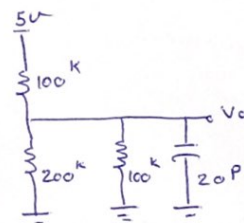
$$V_O(t) = V_O(\infty) + (V_O(0^+) - V_O(\infty)) e^{-\frac{t}{\tau_1}} = -157.5 + (4.95 + 157.5) e^{-\frac{t}{1^{uS}}}$$

$$= -157.5 + 162.45 e^{-\frac{t}{1^{uS}}} \quad \xrightarrow{V_{GS} - V_{th} = 4} \quad 4 = -157.5 + 162.45 e^{-\frac{t}{1^{uS}}}$$

$$\Rightarrow t = 5.86^{nSec}$$

note, by NMOS (triode) \Rightarrow

$$-\left(\frac{t - 5.86}{\tau_2} \right)$$



$$V_O(t) = V_O(\infty) + (V_O(t=5.86) - V_O(\infty)) e^{-\frac{t-5.86}{\tau_2}}$$

$$** : V_O(t) = -157.5 + (4.95 + 157.5) e^{-\frac{t}{1^{uS}}} \xrightarrow{t=5.86^{nS}} V_O(t=5.86^{nS}) = 4^V$$

$$V_O(\infty) :$$

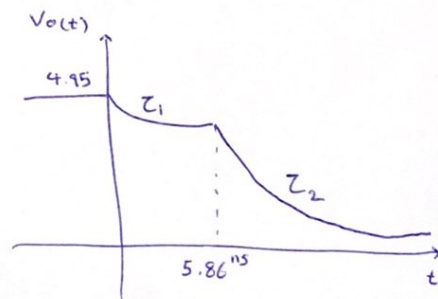
$$\tau_2 = [100^k \parallel 100^k \parallel 200^k] \times 20^{pF} = 3.98^{nS}$$

$$KCL: \frac{V_O(\infty) - 5}{100^k} + \frac{V_O(\infty) - 0}{200^k} + \frac{V_O(\infty) - 0}{100^k} = 0$$

$$\Rightarrow V_O(\infty) = \frac{(200^k \parallel 100^k) \times 5}{(200^k \parallel 100^k) + 100^k} = 0.01^V$$

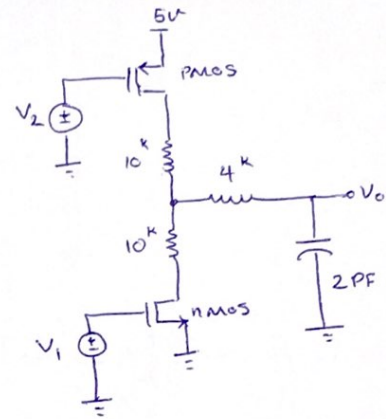
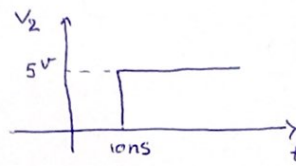
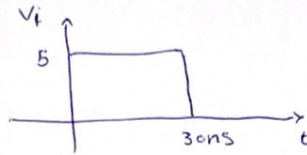
$$\Rightarrow V_O(t) = 0.01 + [4 - 0.01] e^{-\frac{t-5.86}{3.98^{nS}}}$$

$$\Rightarrow V_O(t) = \begin{cases} 4.95 & t \leq 0 \\ -157.5 + 162.45 e^{-\frac{t}{1^{uS}}} & 0 \leq t \leq 5.86^{nS} \\ 0.01 + 3.99 e^{-\left(\frac{t-5.86^{nS}}{3.98^{nS}} \right)} & 5.86 \leq t \leq \infty \end{cases}$$

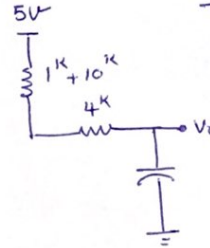


#4-36

$$\begin{cases} R_{nmos} = 200 \Omega \\ R_{pmos} = 1 K \\ k = 0.2 \frac{mA}{V^2} \\ |V_{th}| = 1V \end{cases}$$



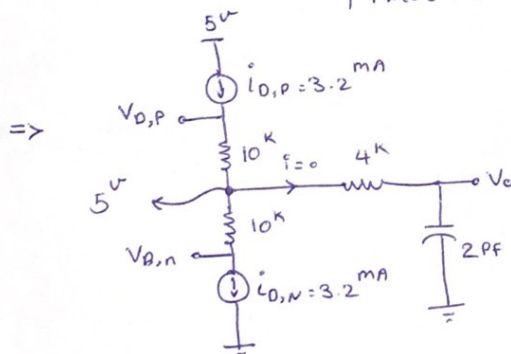
for $t < 0$: $\begin{cases} PMOS : ON \\ NMOS : OFF \end{cases}$ $\xrightarrow{\text{با فرض اینکه هر دو ترانزیستور در حالت اشباع باشند}}$



$$\Rightarrow V_o(t < 0) = 5V \rightarrow \begin{cases} V_{DS, PMOS} = -5V \\ V_{GS} = -5V \\ \Rightarrow V_{DS} \geq V_{GS} - V_{th} \end{cases} \rightarrow \text{فرض درستی است}$$

for $0 < t < 10ns$: $\begin{cases} NMOS : ON \\ PMOS : ON \end{cases}$ $\xrightarrow{\text{با فرض اینکه هر دو ترانزیستور در حالت اشباع باشند}}$

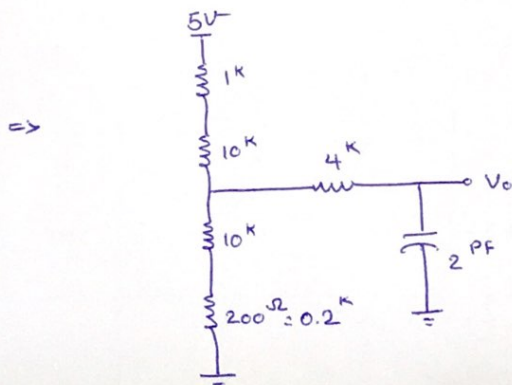
$$\begin{cases} I_{D,P} = k(V_{GS} + V_{th})^2 = 0.2(-5+1)^2 = 3.2 mA \\ I_{D,N} = k(V_{GS} - V_{th})^2 = 0.2(5-1)^2 = 3.2 mA \end{cases}$$



$$V_o(0^-) = V_o(0^+) = 5V$$

$$\begin{cases} \frac{5 - V_{D,P}}{10K} = -3.2 \Rightarrow V_{D,P} = 37V \\ \frac{5 - V_{D,N}}{10K} = 3.2 \Rightarrow V_{D,N} = -27V \end{cases}$$

$$\begin{cases} V_{DS,N} \not\geq V_{GS} - V_{th} : -27 \not\geq 5-1 \quad \times \rightarrow \text{فرض غلط بوده و NMOS در ترانزیستور اشباع نیست} \\ V_{DS,P} \leq V_{GS} - V_{th} : 32 \leq 0+1 \quad \times \rightarrow \text{" " " PMOS " " " } \end{cases}$$

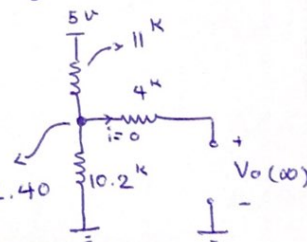


$$V_o(0^-) = V_o(0^+) = 5V$$

$$V_o(\infty) :$$

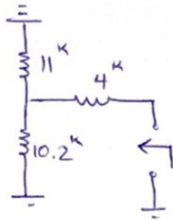
$$\bar{V} = \frac{10.2 \times 5}{10.2 + 11} = 2.40$$

$$\Rightarrow \bar{V} = V_o(\infty) = 2.40V$$



$$\Rightarrow V_o(t) = V_o(\infty) + [V_o(t=0^+) - V_o(\infty)] e^{-\frac{t}{\tau}}$$

$$\tau_1 = RC$$



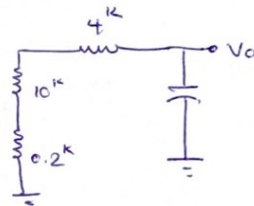
$$R_{TH} = 4k + 11k \parallel 10.2k = 9.3k$$

$$\tau_1 = 2^{PF} \times 9.3k = 18.6 ns$$

$$\Rightarrow V_o(t) = 2.40 + [5 - 2.40] e^{-\frac{t}{18.6 ns}} = 2.40 + 2.6 e^{-\frac{t}{18.6 ns}} \quad \text{for } 0 < t < 10 ns$$

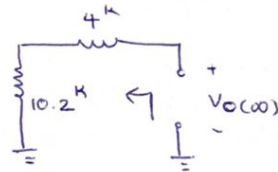
$$\Rightarrow V_o(t = 10 ns) = 2.40 + 2.6 e^{-\frac{10 ns}{18.6 ns}} = \underline{3.9 V}$$

$$\text{for } 10 ns < t < 30 ns : \begin{cases} \text{PMOS: off} \\ \text{NMOS: on} \end{cases}$$

 \Rightarrow


$$V_o(10 ns_-) = V_o(10 ns_+) = 3.9 V$$

$$\Rightarrow V_o(\infty) = 0$$



$$\Rightarrow V_o(\infty) = 0$$

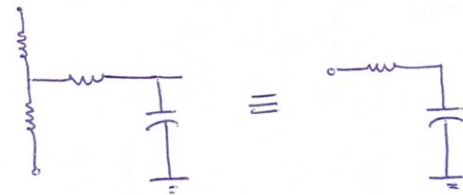
$$\tau_2 = [4k + 10.2k] \times 2^{PF} = 28.4 ns$$

$$-\left(\frac{t - 10 ns}{28.4 ns}\right)$$

$$-\left(\frac{t - 10 ns}{28.4 ns}\right)$$

$$\Rightarrow V_o(t) = 0 + [3.9 - 0] e^{-\left(\frac{t - 10 ns}{28.4 ns}\right)} = 3.9 e^{-\left(\frac{t - 10 ns}{28.4 ns}\right)} \quad \text{for } 10 ns < t < 30 ns$$

$$\text{for } t > 30 ns : \begin{cases} \text{PMOS: off} \\ \text{NMOS: off} \end{cases}$$

 \Rightarrow


$$\Rightarrow V_o(t = 30 ns) = 3.9 e^{-\left(\frac{30 ns - 10 ns}{28.4 ns}\right)} = 1.92 V$$

$$\Rightarrow V_o(t) = \begin{cases} 5 V & t < 0 \\ 2.4 + 2.6 e^{-\frac{t}{18.6 ns}} & 0 < t < 10 ns \\ 3.9 e^{-\left(\frac{t - 10 ns}{28.4 ns}\right)} & 10 ns < t < 30 ns \\ 1.92 & t > 30 ns \end{cases}$$

$$\begin{cases} t < 0 \\ 0 < t < 10 ns \\ 10 ns < t < 30 ns \\ t > 30 ns \end{cases}$$

